

Rong Zhang

List of Publications by Year in descending order

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286
papers

5,832
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87723

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114278

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all docs

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docs citations

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times ranked

6682
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#	ARTICLE	IF	CITATIONS
1	1.2 kV/25 A Normally off P-N Junction/AlGaIn/GaN HEMTs With Nanosecond Switching Characteristics and Robust Overvoltage Capability. IEEE Transactions on Power Electronics, 2022, 37, 26-30.	5.4	18
2	1.95-kV Beveled-Mesa NiO $\hat{1}^2$ -Ga ₂ O ₃ Heterojunction Diode With 98.5% Conversion Efficiency and Over Million-Times Overvoltage Ruggedness. IEEE Transactions on Power Electronics, 2022, 37, 1223-1227.	5.4	60
3	2.41 kV Vertical P-NiO/n-Ga ₂ O ₃ Heterojunction Diodes With a Record Baliga's Figure-of-Merit of 5.18 GW/cm ² . IEEE Transactions on Power Electronics, 2022, 37, 3743-3746.	5.4	72
4	Over 1200 V Normally-OFF p-NiO Gated AlGaIn/GaN HEMTs on Si With a Small Threshold Voltage Shift. IEEE Electron Device Letters, 2022, 43, 268-271.	2.2	9
5	Effect of Current on the Inhomogeneous Light Emission From AlGaInP-Based Flip-Chip Red Mini-LEDs. IEEE Electron Device Letters, 2022, 43, 402-405.	2.2	13
6	Majority and Minority Carrier Traps in NiO $\hat{1}^2$ -Ga ₂ O ₃ p ⁺ -n Heterojunction Diode. IEEE Transactions on Electron Devices, 2022, 69, 981-987.	1.6	23
7	Enhancing deep-UV emission at 234 nm by introducing a truncated pyramid AlN/GaN nanostructure with fine-tuned multiple facets. Nanoscale, 2022, 14, 653-662.	2.8	8
8	Highly responsive and selective ppb-level NO ₂ gas sensor based on porous Pd-functionalized CuO/rGO at room temperature. Journal of Materials Chemistry C, 2022, 10, 3756-3769.	2.7	27
9	70- $\hat{1}^4$ m-Body Ga ₂ O ₃ Schottky Barrier Diode With 1.48 K/W Thermal Resistance, 59 A Surge Current and 98.9% Conversion Efficiency. IEEE Electron Device Letters, 2022, 43, 773-776.	2.2	19
10	Epitaxial Growth and Characteristics of Nonpolar a-Plane InGaIn Films with Blue-Green-Red Emission and Entire In Content Range. Chinese Physics Letters, 2022, 39, 048101.	1.3	4
11	Achieving Record High External Quantum Efficiency >86.7% in Solar-Blind Photoelectrochemical Photodetection. Advanced Functional Materials, 2022, 32, .	7.8	23
12	M-Plane $\hat{1}^2$ -Ga ₂ O ₃ Solar-Blind Detector With Record-High Responsivity-Bandwidth Product and High-Temperature Operation Capability. IEEE Electron Device Letters, 2022, 43, 541-544.	2.2	11
13	3-D Simulation Study of a Normally-OFF GaN Lateral Multi-Channel JFET With Optimized Electrical Field Transfer Terminal Structure. IEEE Transactions on Electron Devices, 2022, 69, 1918-1923.	1.6	1
14	Demonstration of $\hat{1}^2$ -Ga ₂ O ₃ Superjunction-Equivalent MOSFETs. IEEE Transactions on Electron Devices, 2022, 69, 2203-2209.	1.6	15
15	Unlocking the Single-Domain Heteroepitaxy of Orthorhombic $\hat{1}^2$ -Ga ₂ O ₃ via Phase Engineering. ACS Applied Electronic Materials, 2022, 4, 461-468.	2.0	8
16	Ga ₂ O ₃ /GaN Heterostructural Ultraviolet Photodetectors with Exciton-Dominated Ultranarrow Response. ACS Applied Electronic Materials, 2022, 4, 188-196.	2.0	19
17	C-Plane Blue Micro-LED With 1.53 GHz Bandwidth for High-Speed Visible Light Communication. IEEE Electron Device Letters, 2022, 43, 910-913.	2.2	23
18	4H-SiC n-i-p Extreme Ultraviolet Detector With Gradient Doping-Induced Surface Junction. IEEE Electron Device Letters, 2022, 43, 906-909.	2.2	2

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19	Arbitrary coherent distributions in a programmable quantum walk. <i>Physical Review Research</i> , 2022, 4, .	1.3	2
20	Maximal coin-walker entanglement in a ballistic quantum walk. <i>Physical Review A</i> , 2022, 105, .	1.0	5
21	High-Responsivity and Fast-Response Ultraviolet Phototransistors Based on Enhanced p-GaN/AlGaIn/GaN HEMTs. <i>ACS Photonics</i> , 2022, 9, 2040-2045.	3.2	14
22	Self-Intercalation Tunable Interlayer Exchange Coupling in a Synthetic van der Waals Antiferromagnet. <i>Advanced Functional Materials</i> , 2022, 32, .	7.8	10
23	Band alignment and polarization engineering in $\text{In}^{\delta}\text{-Ga}_2\text{O}_3/\text{GaN}$ ferroelectric heterojunction. <i>Science China: Physics, Mechanics and Astronomy</i> , 2022, 65, .	2.0	8
24	Self-Assembly Nanopillar/Superlattice Hierarchical Structure: Boosting AlGaIn Crystalline Quality and Achieving High-Performance Ultraviolet Avalanche Photodetector. <i>ACS Applied Materials & Interfaces</i> , 2022, 14, 33525-33537.	4.0	4
25	3.4-kV AlGaIn/GaN Schottky Barrier Diode on Silicon Substrate With Engineered Anode Structure. <i>IEEE Electron Device Letters</i> , 2021, 42, 208-211.	2.2	20
26	High-performance normally off p-GaN gate high-electron-mobility transistor with $\text{In}_{0.17}\text{Al}_{0.83}\text{N}$ barrier layer design. <i>Optical and Quantum Electronics</i> , 2021, 53, 1.	1.5	7
27	Impurity band assisted carrier relaxation in Cr doped topological insulator Bi_2Se_3 . <i>Applied Physics Letters</i> , 2021, 118, .	1.5	3
28	High sensitivity x-ray detectors based on 4H-SiC p-i-n structure with 80 nm thick intrinsic layer. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2021, 39, .	0.6	1
29	Investigations of Sidewall Passivation Technology on the Optical Performance for Smaller Size GaN-Based Micro-LEDs. <i>Crystals</i> , 2021, 11, 403.	1.0	19
30	Enhanced Stability and Sensitivity of AlGaIn/GaN-HEMTs pH Sensor by Reference Device. <i>IEEE Sensors Journal</i> , 2021, 21, 9771-9776.	2.4	5
31	Vertical Field-Plated NiO/Ga ₂ O ₃ Heterojunction Power Diodes. , 2021, , .		6
32	Demonstration of the p-NiO _x /n-Ga ₂ O ₃ Heterojunction Gate FETs and Diodes With $\text{BV}^2/\text{R}_{\text{on,sp}}$ Figures of Merit of 0.39 GW/cm^2 and 1.38 GW/cm^2 . <i>IEEE Electron Device Letters</i> , 2021, 42, 485-488.	2.2	86
33	Progress on AlGaIn-based solar-blind ultraviolet photodetectors and focal plane arrays. <i>Light: Science and Applications</i> , 2021, 10, 94.	7.7	193
34	High-Reflectivity Mg/Al Ohmic Contacts on n-GaN. <i>IEEE Photonics Technology Letters</i> , 2021, 33, 347-349.	1.3	2
35	High Performance Quasi-Vertical GaN Junction Barrier Schottky Diode with Zero Reverse Recovery and Rugged Avalanche Capability. , 2021, , .		6
36	Room-temperature intrinsic ferromagnetism in epitaxial CrTe ₂ ultrathin films. <i>Nature Communications</i> , 2021, 12, 2492.	5.8	179

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37	Electrode-Dependent Electrical Properties of Detection-Band Tunable Ultraviolet Photodetectors Based on Ga ₂ O ₃ /GaN Heterostructures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2100166.	0.8	1
38	A High Quantum Efficiency Narrow-Band UV-B AlGaIn p-i-n Photodiode With Polarization Assistance. <i>IEEE Photonics Journal</i> , 2021, 13, 1-8.	1.0	5
39	High-Voltage Quasi-Vertical GaN Junction Barrier Schottky Diode With Fast Switching Characteristics. <i>IEEE Electron Device Letters</i> , 2021, 42, 974-977.	2.2	29
40	46.4: Fabrication of InGaIn/GaN-based nano-LEDs for display applications. <i>Digest of Technical Papers SID International Symposium</i> , 2021, 52, 568-568.	0.1	0
41	Tuning interfacial spin pump in Ta/CoFeB/MgO films by ultrafast laser pulse. <i>Applied Physics Letters</i> , 2021, 119, 092404.	1.5	1
42	Giant Topological Hall Effect in van der Waals Heterostructures of CrTe ₂ /Bi ₂ Te ₃ . <i>ACS Nano</i> , 2021, 15, 15710-15719.	7.3	34
43	Growth and nitridation of $\hat{2}$ -Ga ₂ O ₃ thin films by Sol-Gel spin-coating epitaxy with post-annealing process. <i>Journal of Sol-Gel Science and Technology</i> , 2021, 100, 183-191.	1.1	10
44	Three-dimensional monolithic micro-LED display driven by atomically thin transistor matrix. <i>Nature Nanotechnology</i> , 2021, 16, 1231-1236.	15.6	120
45	Shift and Recovery Mechanisms of p-GaN Gate HEMTs Under DC/AC Gate Stress Investigated by Fast Sweeping Characterization. <i>IEEE Electron Device Letters</i> , 2021, 42, 1508-1511.	2.2	17
46	Demonstration of Avalanche and Surge Current Robustness in GaN Junction Barrier Schottky Diode With 600-V/10-A Switching Capability. <i>IEEE Transactions on Power Electronics</i> , 2021, 36, 12163-12167.	5.4	19
47	1.37 kV/12 A NiO/ $\hat{2}$ -Ga ₂ O ₃ Heterojunction Diode With Nanosecond Reverse Recovery and Rugged Surge-Current Capability. <i>IEEE Transactions on Power Electronics</i> , 2021, 36, 12213-12217.	5.4	77
48	Band Alignment and Enhanced Interfacial Conductivity Manipulated by Polarization in a Surfactant-Mediated Grown \hat{p} -Ga ₂ O ₃ /In ₂ O ₃ Heterostructure. <i>ACS Applied Electronic Materials</i> , 2021, 3, 795-803.	2.0	15
49	Optimization of annealing conditions for Ag/p-GaN ohmic contacts. <i>Applied Physics A: Materials Science and Processing</i> , 2021, 127, 870.	1.1	6
50	Low-Voltage p-i-n GaN-Based Alpha-Particle Detector With High Energy Resolution. <i>IEEE Electron Device Letters</i> , 2021, 42, 1755-1758.	2.2	3
51	Field-Plated NiO/Ga ₂ O ₃ p-n Heterojunction Power Diodes With High-Temperature Thermal Stability and Near Unity Ideality Factors. <i>IEEE Journal of the Electron Devices Society</i> , 2021, 9, 1166-1171.	1.2	10
52	1000-W Resistive Energy Dissipating Capability Against Inductive Transients Demonstrated in Non-Avalanche AlGaIn/GaN Schottky Diode. <i>IEEE Electron Device Letters</i> , 2021, 42, 1743-1746.	2.2	4
53	Monolithic 3D μ -LED displays through BEOL integration of large-area MoS ₂ TFT matrix. , 2021, , .		2
54	A Selective Etching Route for Large-Scale Fabrication of $\hat{2}$ -Ga ₂ O ₃ Micro-/Nanotube Arrays. <i>Nanomaterials</i> , 2021, 11, 3327.	1.9	7

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55	Hybrid Light Emitters and UV Solar-Blind Avalanche Photodiodes based on III-Nitride Semiconductors. <i>Advanced Materials</i> , 2020, 32, e1904354.	11.1	34
56	Synthesis and Properties of InGaN/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 1900729.	0.8	4
57	Improved Performance of Hybrid Organic/Inorganic p-n Heterojunction White Light-Emitting Diodes with 4,4'-Cyclohexane-1,1'-diylbis[N,N-bis(4-methylphenyl)aniline] as a Multifunctional Hole Transport Layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 1900763.	0.8	0
58	Electronic properties of arsenene nanoribbons for FET application. <i>Optical and Quantum Electronics</i> , 2020, 52, 1.	1.5	3
59	Charge transfer dynamics of the CdTe quantum dots fluorescence quenching induced by ferrous (II) ions. <i>Applied Physics Letters</i> , 2020, 116, 012105.	1.5	8
60	High- k HfO ₂ -Based AlGaIn/GaN MIS-HEMTs With Y ₂ O ₃ Interfacial Layer for High Gate Controllability and Interface Quality. <i>IEEE Journal of the Electron Devices Society</i> , 2020, 8, 15-19.	1.2	19
61	Electron-Beam-Driven III-Nitride Plasmonic Nanolasers in the Deep-UV and Visible Region. <i>Small</i> , 2020, 16, 1906205.	5.2	10
62	Direct observation of ferrimagnetic ordering in inverse Heusler alloy Mn ₂ CoAl. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	5
63	Improved Performance of Hybrid Organic/Inorganic p-n Heterojunction White Light-Emitting Diodes with 4,4'-Cyclohexane-1,1'-diylbis[N,N-bis(4-methylphenyl)aniline] as a Multifunctional Hole Transport Layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 2070029.	0.8	0
64	Bi ₂ O ₂ Se/Au-Based Schottky Phototransistor With Fast Response and Ultrahigh Responsivity. <i>IEEE Electron Device Letters</i> , 2020, 41, 1464-1467.	2.2	5
65	Strong interface-induced spin-charge conversion in YIG/Cr heterostructures. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	12
66	Different λ Behaviors and Leakage Current Mechanisms in AlGaIn Solar-Blind Ultraviolet Avalanche Photodiodes. <i>ACS Applied Electronic Materials</i> , 2020, 2, 2716-2720.	2.0	3
67	Manipulation of Gilbert damping in ultrathin half-metallic Co ₂ FeAl _{1+x} by composition-deficiency-compensation. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	7
68	Direct observation of reach-through behavior in back-illuminated algan avalanche photodiode with separate absorption and multiplication structure. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 425101.	1.3	3
69	Synthesis and Properties of InGaIn/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 2070028.	0.8	0
70	μ -Ga ₂ O ₃ : A Promising Candidate for High-Electron-Mobility Transistors. <i>IEEE Electron Device Letters</i> , 2020, , 1-1.	2.2	15
71	High-Performance 4H-SiC Schottky Photodiode With Semitransparent Grid-Electrode for EUV Detection. <i>IEEE Photonics Technology Letters</i> , 2020, 32, 791-794.	1.3	10
72	After-Pulse Characterizations of Geiger-Mode 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2020, 32, 706-709.	1.3	5

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73	Polarization-independent Indium Phosphide Nanowire Photodetectors. <i>Advanced Optical Materials</i> , 2020, 8, 2000514.	3.6	9
74	Realization of regular resonance mode in GaN-based polygonal microdisks on Si. <i>Journal of Applied Physics</i> , 2020, 127, 113102.	1.1	3
75	Band Alignment and Interface Recombination in NiO I^2 -Ga $\text{sub}2\text{/sub}$ O $\text{sub}3\text{/sub}$ Type-II p-n Heterojunctions. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 3341-3347.	1.6	63
76	High-responsivity Graphene/4H-SiC Ultraviolet Photodetector Based on a Planar Junction Formed by the Dual Modulation of Electric and Light Fields. <i>Advanced Optical Materials</i> , 2020, 8, 2000559.	3.6	19
77	Anion Engineering Enhanced Response Speed and Tunable Spectral Responsivity in Gallium-Oxynitrides-Based Ultraviolet Photodetectors. <i>ACS Applied Electronic Materials</i> , 2020, 2, 808-816.	2.0	18
78	Do all screw dislocations cause leakage in GaN-based devices?. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	38
79	Investigation of the Electroluminescence Mechanism of GaN-Based Blue and Green Light-Emitting Diodes with Junction Temperature Range of 120-373 K. <i>Applied Sciences (Switzerland)</i> , 2020, 10, 444.	1.3	18
80	Highly Enhanced Inductive Current Sustaining Capability and Avalanche Ruggedness in GaN p-i-n Diodes With Shallow Bevel Termination. <i>IEEE Electron Device Letters</i> , 2020, 41, 469-472.	2.2	16
81	Mg acceptor activation mechanism and hole transport characteristics in highly Mg-doped AlGaIn alloys. <i>Chinese Physics B</i> , 2020, 29, 058103.	0.7	3
82	1.4-kV Quasi-Vertical GaN Schottky Barrier Diode With Reverse p-n Junction Termination. <i>IEEE Journal of the Electron Devices Society</i> , 2020, 8, 316-320.	1.2	20
83	Element-specific spin and orbital moments and perpendicular magnetic anisotropy in Ta/CoFeB/MgO structures. <i>Journal of Applied Physics</i> , 2020, 127, .	1.1	3
84	Property manipulation through pulsed laser annealing in high dose Mg-implanted GaN. <i>Journal of Applied Physics</i> , 2020, 128, .	1.1	5
85	Light-Tunable Ferromagnetism in Atomically Thin Fe_3Si Driven by Femtosecond Laser Pulse. <i>Physical Review Letters</i> , 2020, 125, 267205.	2.9	57
86	Solar-blind ultraviolet photodetector based on vertically aligned single-crystalline $\text{I}^2\text{-Ga}_2\text{O}_3$ nanowire arrays. <i>Nanophotonics</i> , 2020, 9, 4497-4503.	2.9	35
87	Layered Topological Insulators and Semimetals for Magnetoresistance Type Sensors. <i>Advanced Quantum Technologies</i> , 2019, 2, 1800039.	1.8	10
88	Evidence of anisotropic Landau level splitting in topological semimetal ZrSiS under high magnetic fields. <i>Frontiers of Physics</i> , 2019, 14, 1.	2.4	0
89	Electrolyte gate controlled metal-insulator transitions of the CaZrO 3 /SrTiO 3 heterointerface. <i>Applied Physics Letters</i> , 2019, 115, 061601.	1.5	14
90	A High-Performance SiO 2 /SiN x 1-D Photonic Crystal UV Filter Used for Solar-Blind Photodetectors. <i>IEEE Photonics Journal</i> , 2019, 11, 1-7.	1.0	3

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91	Precise Extraction of Dynamic χ Under High Frequency and High Voltage by a Double-Diode-Isolation Method. IEEE Journal of the Electron Devices Society, 2019, 7, 690-695.	1.2	10
92	Sensitive and Ultrabroadband Phototransistor Based on Two-Dimensional $\text{Bi}_2\text{O}_2\text{Se}$ Nanosheets. Advanced Functional Materials, 2019, 29, 1905806.	7.8	106
93	Single-crystal GaN layer converted from $\text{In}_2\text{Ga}_2\text{O}_3$ films and its application for free-standing GaN. CrystEngComm, 2019, 21, 1224-1230.	1.3	10
94	Janus Ga_2SeTe : A Promising Candidate for Highly Efficient Solar Cells. Solar Rrl, 2019, 3, 1900321.	3.1	13
95	Strain-driven lattice distortion and the resultant magnetic properties of $\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3/\text{BaTiO}_3$ superlattices. Applied Physics Letters, 2019, 115, 201604.	1.5	4
96	All-carbon hybrids for high-performance electronics, optoelectronics and energy storage. Science China Information Sciences, 2019, 62, 1.	2.7	6
97	23.3: Invited Paper: Hybrid III-Nitride/Nanocrystals White Light-Emitting Diodes. Digest of Technical Papers SID International Symposium, 2019, 50, 225-227.	0.1	0
98	Effect of Very High-Fluence Proton Radiation on 6H-SiC Photoconductive Proton Detectors. IEEE Electron Device Letters, 2019, 40, 1929-1932.	2.2	10
99	Optical Performance of Top-Down Fabricated AlGaIn Nanorod Arrays with Multi-Quantum Wells Embedded. Nanoscale Research Letters, 2019, 14, 170.	3.1	2
100	Tailoring exciton dynamics of monolayer transition metal dichalcogenides by interfacial electron-phonon coupling. Communications Physics, 2019, 2, .	2.0	27
101	Ultrafast Orbital-Oriented Control of Magnetization in Half-Metallic $\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$ Films. Advanced Materials, 2019, 31, e1806443.	11.1	13
102	Gate Reliability of p-GaN Gate AlGaIn/GaN High Electron Mobility Transistors. IEEE Electron Device Letters, 2019, 40, 379-382.	2.2	21
103	Observation of Small Polaron and Acoustic Phonon Coupling in Ultrathin $\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3/\text{SrTiO}_3$ Structures. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1800657.	1.2	2
104	Highly Narrow-Band Polarization-Sensitive Solar-Blind Photodetectors Based on $\text{In}_2\text{Ga}_2\text{O}_3$ Single Crystals. ACS Applied Materials & Interfaces, 2019, 11, 7131-7137.	4.0	55
105	Performance Modulation for Back-Illuminated AlGaIn Ultraviolet Avalanche Photodiodes Based on Multiplication Scaling. IEEE Photonics Journal, 2019, 11, 1-7.	1.0	10
106	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. Scientific Reports, 2019, 9, 8796.	1.6	24
107	On-chip engineering of high-dimensional path-entangled states in a quadratic coupled-waveguide system. Physical Review A, 2019, 99, .	1.0	6
108	Performance of Monolayer Blue Phosphorene Double-Gate MOSFETs from the First Principles. ACS Applied Materials & Interfaces, 2019, 11, 20956-20964.	4.0	39

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109	Ultrafast free carrier dynamics in black phosphorus/molybdenum disulfide (BP/MoS ₂) heterostructures. <i>Nanoscale Horizons</i> , 2019, 4, 1099-1105.	4.1	36
110	Investigation on the Activation Energy of Device Degradation and Switching Time in AlGaIn/GaN HEMTs for High-Frequency Application. <i>IEEE Journal of the Electron Devices Society</i> , 2019, 7, 417-424.	1.2	5
111	Experimental observation of dual magnetic states in topological insulators. <i>Science Advances</i> , 2019, 5, eaav2088.	4.7	18
112	Spatial Non-Uniform Hot Carrier Luminescence From 4H-SiC p-i-n Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2019, 31, 447-450.	1.3	6
113	Observation and Modeling of Leakage Current in AlGaIn Ultraviolet Light Emitting Diodes. <i>IEEE Photonics Technology Letters</i> , 2019, 31, 1697-1700.	1.3	4
114	Effects of dissipative substrate on the performances of enhancement mode AlInN/GaN HEMTs. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2019, 32, e2482.	1.2	4
115	Carbonized Bamboos as Excellent 3D Solar Vapor Generation Devices. <i>Advanced Materials Technologies</i> , 2019, 4, 1800593.	3.0	107
116	Topological Phase Transition-Induced Triaxial Vector Magnetoresistance in (Bi _{1-x} In _x) ₂ Se ₃ Nanodevices. <i>ACS Nano</i> , 2018, 12, 1537-1543.	7.3	13
117	Direct Demonstration of the Emergent Magnetism Resulting from the Multivalence Mn in a LaMnO ₃ Epitaxial Thin Film System. <i>Advanced Electronic Materials</i> , 2018, 4, 1800055.	2.6	27
118	Vertical 4H-SiC n-i-p-n APDs With Partial Trench Isolation. <i>IEEE Photonics Technology Letters</i> , 2018, 30, 805-808.	1.3	9
119	A Reusable and High Sensitivity Nitrogen Dioxide Sensor Based on Monolayer SnSe. <i>IEEE Electron Device Letters</i> , 2018, 39, 599-602.	2.2	43
120	Transport evidence of 3D topological nodal-line semimetal phase in ZrSiS. <i>Frontiers of Physics</i> , 2018, 13, 1.	2.4	30
121	Effective suppression of the high temperature DC performance degradation of AlInN/GaN HEMTs by back barrier. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2018, 31, e2299.	1.2	1
122	Effects of the Trap Level in the Unintentionally Doped GaN Buffer Layer on Optimized p-GaN Gate AlGaIn/GaN HEMTs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700368.	0.8	5
123	First-principles insights on the electronic and optical properties of ZnO@CNT core@shell nanostructure. <i>Scientific Reports</i> , 2018, 8, 15464.	1.6	14
124	Highly efficient solar steam generation by hybrid plasmonic structured TiN/mesoporous anodized alumina membrane. <i>Journal of Materials Research</i> , 2018, 33, 3857-3869.	1.2	19
125	Enhanced p-type conduction in AlGaIn grown by metal-source flow-rate modulation epitaxy. <i>Applied Physics Letters</i> , 2018, 113, .	1.5	17
126	Vertically Emitting Indium Phosphide Nanowire Lasers. <i>Nano Letters</i> , 2018, 18, 3414-3420.	4.5	33

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127	Avalanche Ruggedness of GaN p-i-n Diodes Grown on Sapphire Substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1800069.	0.8	7
128	Identification and modulation of electronic band structures of single-phase $\text{In}_{2-x}\text{Al}_x\text{Ga}_x\text{O}_3$ alloys grown by laser molecular beam epitaxy. <i>Applied Physics Letters</i> , 2018, 113, .	1.5	43
129	The Effect of the Original Thickness of Ag in the Graphene-Ag Nanodots Transparent Conductive Layer on the Electrical and Optical Properties of GaN-Based UV-LEDs. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 3803-3808.	1.6	5
130	High Sensitive pH Sensor Based on AlInN/GaN Heterostructure Transistor. <i>Sensors</i> , 2018, 18, 1314.	2.1	13
131	Ultrahigh Hall mobility and suppressed backward scattering in layered semiconductor Bi ₂ O ₂ Se. <i>Applied Physics Letters</i> , 2018, 113, .	1.5	27
132	Observation of bimolecular recombination in high mobility semiconductor Bi ₂ O ₂ Se using ultrafast spectroscopy. <i>Applied Physics Letters</i> , 2018, 113, 061104.	1.5	10
133	Photoresponsivity of an all-semimetal heterostructure based on graphene and WTe ₂ . <i>Scientific Reports</i> , 2018, 8, 12840.	1.6	14
134	Tailored Emission Properties of ZnTe/ZnTe:O/ZnO Core-Shell Nanowires Coupled with an Al Plasmonic Bowtie Antenna Array. <i>ACS Nano</i> , 2018, 12, 7327-7334.	7.3	8
135	Emergent Ferromagnetism: Direct Demonstration of the Emergent Magnetism Resulting from the Multivalence Mn in a LaMnO ₃ Epitaxial Thin Film System (<i>Adv. Electron. Mater.</i> 6(2018). <i>Advanced Electronic Materials</i> , 2018, 4, 1870030.	2.6	1
136	A robust and tuneable mid-infrared optical switch enabled by bulk Dirac fermions. <i>Nature Communications</i> , 2017, 8, 14111.	5.8	174
137	Unsaturated magnetoconductance of epitaxial La _{0.7} Sr _{0.3} MnO ₃ thin films in pulsed magnetic fields up to 60 T. <i>AIP Advances</i> , 2017, 7, 056404.	0.6	7
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